



# ISPlasma2021/ IC-PLANTS2021

13th International Symposium on Advanced Plasma Science  
and its Applications for Nitrides and Nanomaterials  
14th International Conference on Plasma-Nano Technology & Science

March 7-11, 2021  
**VIRTUAL SYMPOSIUM**

## Organizing Committee

### Chairperson

Masafumi Ito, Meijo University

### Vice-Chairperson

Koh Matsumoto, Nagoya University

Noriyasu Ohno, Nagoya University

Yoshimi Watanabe, Nagoya Institute of Technology

Sponsored by : The Japan Society of Applied Physics

Co-Sponsored by : Nagoya University Nagoya Institute of Technology Meijo University  
Chubu University

<http://www.isplasma.jp/>



## Registration

Advanced Online Registration is required.

Registration Fee : Early Registration (Until Jan 31, 2021)

Late Registration

Tutorial Fee : Participant in Main Symposium

Tutorial Registration Only

General Student

JPY 45,000 JPY 15,000

JPY 50,000 JPY 20,000

JPY 1,000 JPY 1,000

JPY 10,000 JPY 3,000

\* Refunds cannot be made at any reason.

ISPlasma/IC-PLANTS is a specialized international symposium that brings together about 1,000 world-leading scientists and engineers in Nagoya, Japan to discuss latest researches in the fields of advanced plasma science, its applications for processing and manufacturing of nitrides and nanomaterials, as well as new systems for technology transfers. This symposium will address issues such as global warming, resources and energy problems to which advanced plasma science and its application technologies can greatly contribute. In this symposium biosensing technologies will be also highlighted, because of their increasing importance in healthcare, agri-food and environmental areas. We hope that this symposium will provide an ideal venue for the exchange of new ideas and information, and also support the initiation or further development of international collaborations among those who work in these multidisciplinary fields.

### Related Fields

#### Plasma Science & Technologies

- Plasma Source
- Plasma in Liquid
- Flexible Electronics
- Advanced Plasma Diagnostics
- Thin Film Deposition Process
- Plasma for Nano & Green Technologies
- Modeling & Simulation
- Etching Process

#### Nitride Semiconductors

- Crystal Growth of GaN & Related Materials
- Device Processing
- MBE Growth & Nitrogen Source
- Optical & Optoelectronic Devices
- Characterization
- Electron & Power Devices

#### Nanomaterials

- Nanodots & Nanoparticles
- 2D Materials
- Composites & Functionally Graded Materials
- Applications for Energy & Environment
- Nanotubes, Nanowires & Nanorods
- Porous Materials & Membranes
- Surface Modification & Functionalization
- Nanomedicine & Sensing

#### Bio Applications

- Plasma Biology & Medicine
- Biomaterials
- Bioimaging
- Biosensors
- Plasma Agriculture
- Biomarkers
- Biodevices, uTAS, Lab on a Chip
- Device Fabrication Technologies

### Abstract Submission

Online abstract submission (one-page English) is available from <http://www.isplasma.jp/>

**Submission Deadline : Friday, October 16, 2020 JST**

### Special Issue

Selected papers will be published in a special issue of a scientific journal.

### Tutorial

Tutorial for Plasma Science, Nitride Semiconductors Nanomaterials and Bio Applications will be held.

## Contact

Secretariat : Inter Group Corp.  
E-mail : [isplasma2021@intergroup.co.jp](mailto:isplasma2021@intergroup.co.jp) Website : <http://www.isplasma.jp/>

# PROGRAM

## Plenary Speakers

A. Yoshino (Meijo University, Asahi Kasei Corp., JAPAN)

## Keynote Speakers

J.P. Booth (CNRS at LPP, FRANCE)

M. Fujii (Kobe University, JAPAN)

T. Kachi (Nagoya University, JAPAN)

S. Toyokuni (Nagoya University, JAPAN)

## Invited Speakers

P. J. Bruggeman (University of Minnesota, USA)

D. Boonyawan (Chiang Mai University, THAILAND)

E. H. Choi (Kwangoon University, KOREA)

S. Graham (Georgia Institute of Technology, USA)

M. Hori (Nagoya University, JAPAN)

K. Ide (Tokyo Institute of Technology, JAPAN)

T. Kaneko (Tohoku University, JAPAN)

M. Keidar (The George Washington University, USA)

A. Kohno (Fukuoka University, JAPAN)

Y. Koide (National Institute for Materials Science, JAPAN)

S. Konstantinidis (University of Mons, BELGIUM)

J. S. Kwon (Yonsei University College of Dentistry, KOREA)

Y. Lin (National Synchrotron Radiation Research Center, TAIWAN)

B. Locke (Florida State University, USA)

## Invited Speakers

G. Muziol (UNIPRESS, POLAND)

K. Nakazato (Nagoya University, JAPAN)

C. Nishigori (Kobe University, JAPAN)

K. Ohkawa (King Abdullah University of Science and Technology, SAUDI ARABIA)

A. Rousseau (LPP, Ecole Polytechnique, FRANCE)

S. Sato (National Institutes for Quantum and Radiological Science and Technology, JAPAN)

H. Shi (Xi'an Jiaotong University, CHINA)

M. Shikida (Hiroshima City University, JAPAN)

T. Takenobu (Nagoya University, JAPAN)

T. Tatsumi (Sony Semiconductor Solutions Corporation, JAPAN)

X. Wang (Peking University, CHINA)

T. von Woedtke (Leibniz Institute for Plasma Science and Technology, INP Greifswald, GERMANY)

H. G. Xing (Cornell University, USA)

X. Zhao (Shenzhen Yick Xin Technology Development, Ltd. Co., CHINA)

## Tutorial Speakers

T. P. Chow (Rensselaer Polytechnic Institute, USA)

U. Czarnetzki (Rhur-Universitat Bochum, GERMANY)

D. Graves (UC Berkley, USA)

L. Miao (Guilin University of Electronic Technology, CHINA)